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"[Embedded - Microcontrollers](#)" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "[Embedded - Microcontrollers](#)"

Details

Product Status	Not For New Designs
Core Processor	ARM® Cortex®-M4
Core Size	32-Bit Single-Core
Speed	84MHz
Connectivity	I ² C, IrDA, LINbus, SDIO, SPI, UART/USART, USB OTG
Peripherals	Brown-out Detect/Reset, DMA, I ² S, POR, PWM, WDT
Number of I/O	36
Program Memory Size	512KB (512K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	96K x 8
Voltage - Supply (Vcc/Vdd)	1.7V ~ 3.6V
Data Converters	A/D 10x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	49-UFBGA, WLCSP
Supplier Device Package	49-WLCSP (2.97x2.97)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32f401cey6btr

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2.1 Compatibility with STM32F4 series

The STM32F401xB/STM32F401xC are fully software and feature compatible with the STM32F4 series (STM32F42x, STM32F43x, STM32F41x, STM32F405 and STM32F407)

The STM32F401xB/STM32F401xC can be used as drop-in replacement of the other STM32F4 products but some slight changes have to be done on the PCB board.

Figure 1. Compatible board design for LQFP100 package

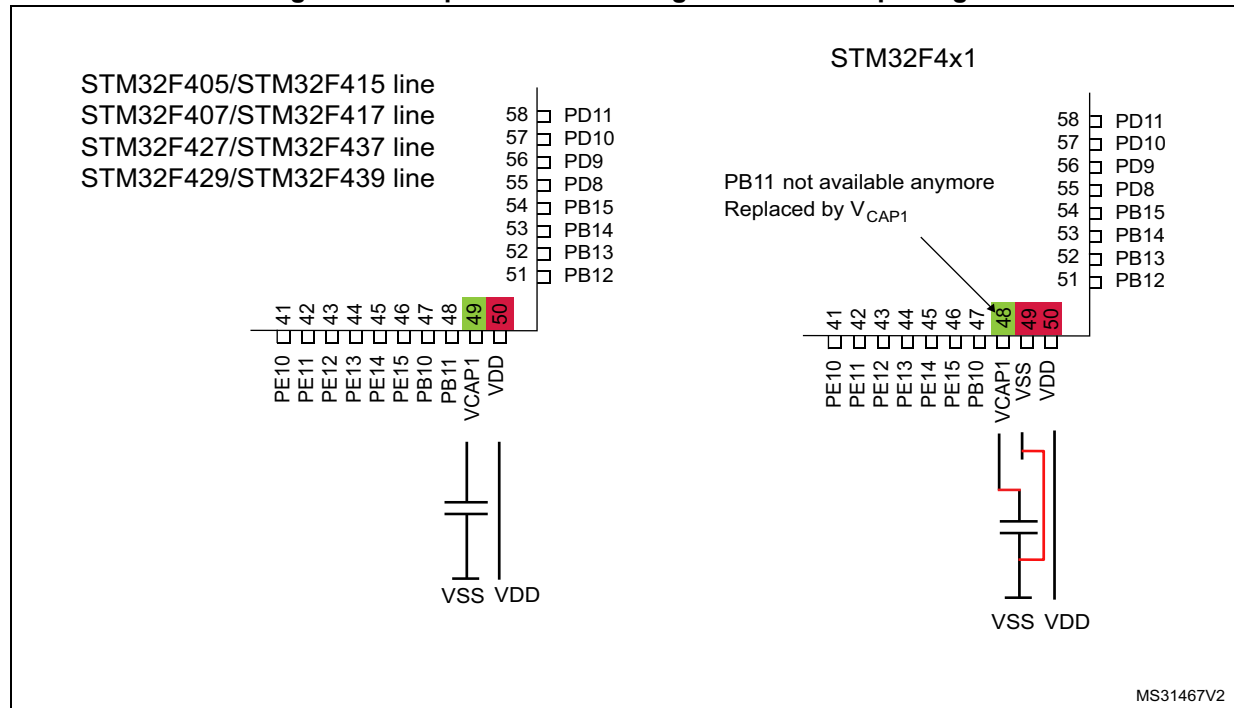
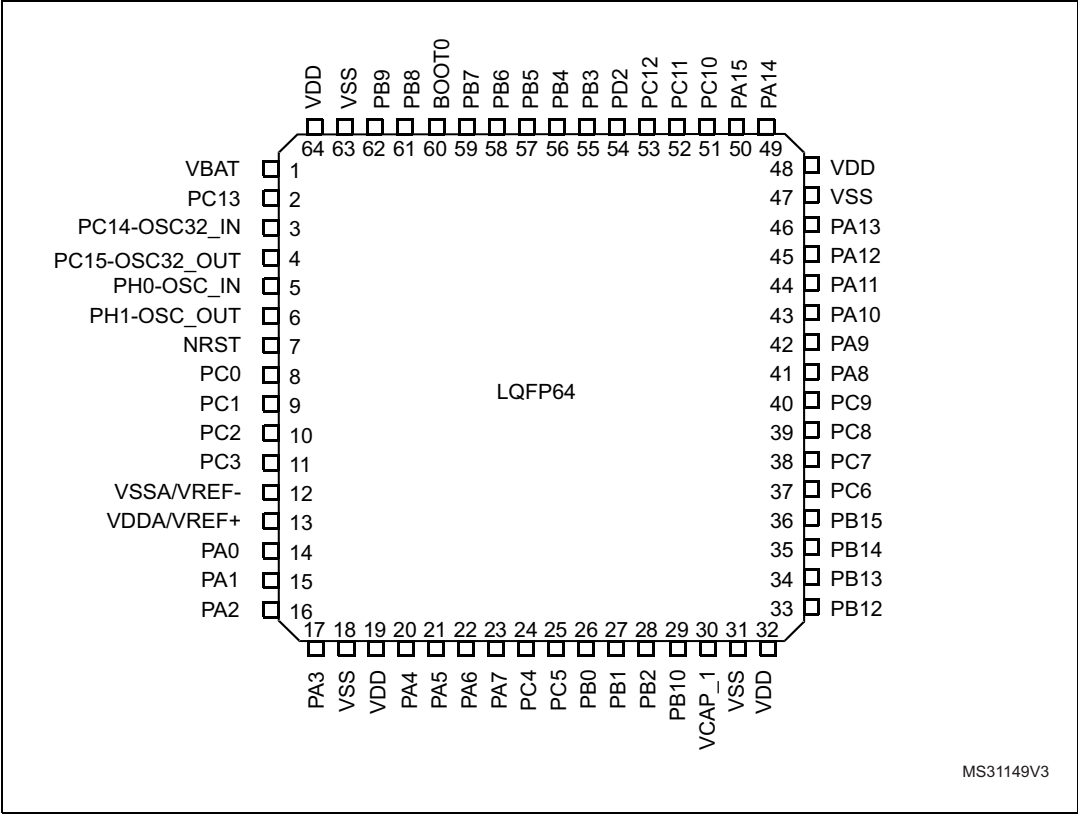


Figure 12. STM32F401xB/STM32F401xC LQFP64 pinout



1. The above figure shows the package top view.

Table 8. STM32F401xB/STM32F401xC pin definitions (continued)

Pin Number					Pin name (function after reset) ⁽¹⁾	Pin type	I/O structure	Notes	Alternate functions	Additional functions
UQFN48	WLCSP49	LQFP64	LQFP100	UFBGA100						
-	-	-	82	B9	PD1	I/O	FT	-	EVENTOUT	-
-	-	54	83	C8	PD2	I/O	FT	-	TIM3_ETR, SDIO_CMD, EVENTOUT	-
-	-	-	84	B8	PD3	I/O	FT	-	SPI2_SCK/I2S2_CK, USART2_CTS, EVENTOUT	-
-	-	-	85	B7	PD4	I/O	FT	-	USART2_RTS, EVENTOUT	-
-	-	-	86	A6	PD5	I/O	FT	-	USART2_TX, EVENTOUT	-
-	-	-	87	B6	PD6	I/O	FT	-	SPI3_MOSI/I2S3_SD, USART2_RX, EVENTOUT	-
-	-	-	88	A5	PD7	I/O	FT	-	USART2_CK, EVENTOUT	-
39	A3	55	89	A8	PB3 (JTDO-SWO)	I/O	FT	-	JTDO-SWO, SPI1_SCK, SPI3_SCK/I2S3_CK, I2C2_SDA, TIM2_CH2, EVENTOUT	-
40	A4	56	90	A7	PB4 (NJTRST)	I/O	FT	-	NJTRST, SPI1_MISO, SPI3_MISO, I2S3ext_SD, I2C3_SDA, TIM3_CH1, EVENTOUT	-
41	B4	57	91	C5	PB5	I/O	FT	-	SPI1_MOSI, SPI3_MOSI/I2S3_SD, I2C1_SMBA, TIM3_CH2, EVENTOUT	-
42	C4	58	92	B5	PB6	I/O	FT	-	I2C1_SCL, USART1_TX, TIM4_CH1, EVENTOUT	-
43	D4	59	93	B4	PB7	I/O	FT	-	I2C1_SDA, USART1_RX, TIM4_CH2, EVENTOUT	-
44	A5	60	94	A4	BOOT0	I	B	-	-	V _{PP}
45	B5	61	95	A3	PB8	I/O	FT	-	I2C1_SCL, TIM4_CH3, TIM10_CH1, SDIO_D4, EVENTOUT	-
46	C5	62	96	B3	PB9	I/O	FT	-	SPI2_NSS/I2S2_WS, I2C1_SDA, TIM4_CH4, TIM11_CH1, SDIO_D5, EVENTOUT	-
-	-	-	97	C3	PE0	I/O	FT	-	TIM4_ETR, EVENTOUT	-
-	-	-	98	A2	PE1	I/O	FT	-	EVENTOUT	-

6 Electrical characteristics

6.1 Parameter conditions

Unless otherwise specified, all voltages are referenced to V_{SS} .

6.1.1 Minimum and maximum values

Unless otherwise specified the minimum and maximum values are guaranteed in the worst conditions of ambient temperature, supply voltage and frequencies by tests in production on 100% of the devices with an ambient temperature at $T_A = 25\text{ }^{\circ}\text{C}$ and $T_A = T_{A\text{max}}$ (given by the selected temperature range).

Data based on characterization results, design simulation and/or technology characteristics are indicated in the table footnotes and are not tested in production. Based on characterization, the minimum and maximum values refer to sample tests and represent the mean value plus or minus three times the standard deviation (mean $\pm 3\sigma$).

6.1.2 Typical values

Unless otherwise specified, typical data are based on $T_A = 25\text{ }^{\circ}\text{C}$, $V_{DD} = 3.3\text{ V}$ (for the $1.7\text{ V} \leq V_{DD} \leq 3.6\text{ V}$ voltage range). They are given only as design guidelines and are not tested.

Typical ADC accuracy values are determined by characterization of a batch of samples from a standard diffusion lot over the full temperature range, where 95% of the devices have an error less than or equal to the value indicated (mean $\pm 2\sigma$).

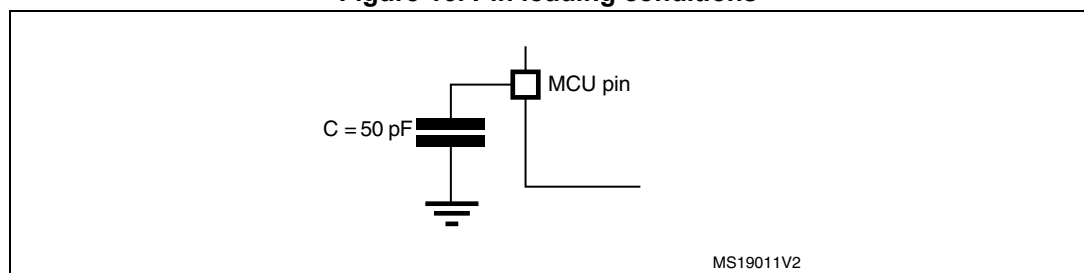
6.1.3 Typical curves

Unless otherwise specified, all typical curves are given only as design guidelines and are not tested.

6.1.4 Loading capacitor

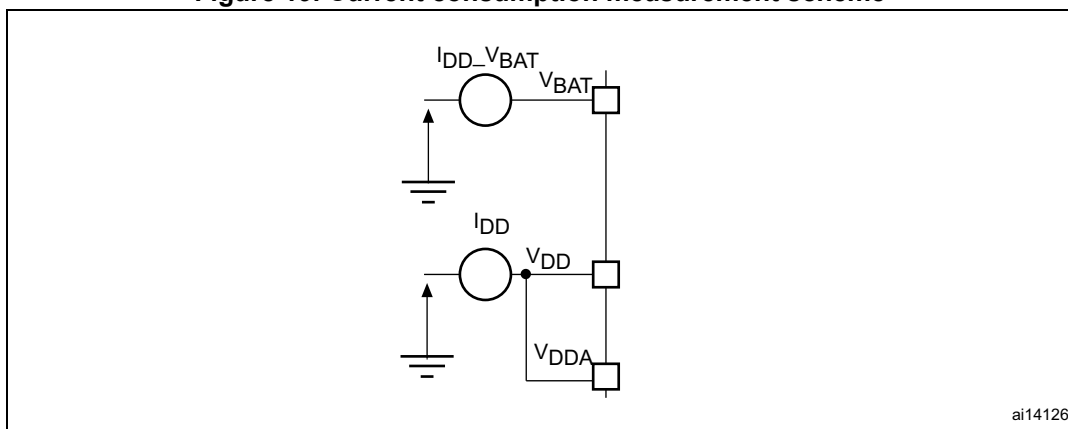
The loading conditions used for pin parameter measurement are shown in [Figure 16](#).

Figure 16. Pin loading conditions



6.1.7 Current consumption measurement

Figure 19. Current consumption measurement scheme



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6.2 Absolute maximum ratings

Stresses above the absolute maximum ratings listed in [Table 11: Voltage characteristics](#), [Table 12: Current characteristics](#), and [Table 13: Thermal characteristics](#) may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these conditions is not implied. Exposure to maximum rating conditions for extended periods may affect device reliability. Device mission profile (application conditions) is compliant with JEDEC JESD47 Qualification Standard. Extended mission profiles are available on demand.

Table 11. Voltage characteristics

Symbol	Ratings	Min	Max	Unit
$V_{DD}-V_{SS}$	External main supply voltage (including V_{DDA} , V_{DD} and V_{BAT}) ⁽¹⁾	-0.3	4.0	V
V_{IN}	Input voltage on FT pins ⁽²⁾	$V_{SS}-0.3$	$V_{DD}+4.0$	
	Input voltage on any other pin	$V_{SS}-0.3$	4.0	
	Input voltage for BOOT0	V_{SS}	9.0	
$ \Delta V_{DDx} $	Variations between different V_{DD} power pins	-	50	mV
$ V_{SSx}-V_{SS} $	Variations between all the different ground pins including V_{REF-}	-	50	
$V_{ESD(HBM)}$	Electrostatic discharge voltage (human body model)	see Section 6.3.14: Absolute maximum ratings (electrical sensitivity)		

1. All main power (V_{DD} , V_{DDA}) and ground (V_{SS} , V_{SSA}) pins must always be connected to the external power supply, in the permitted range.
2. V_{IN} maximum value must always be respected. Refer to [Table 12](#) for the values of the maximum allowed injected current.

Table 25. Typical and maximum current consumption in run mode, code with data processing (ART accelerator enabled with prefetch) running from Flash memory

Symbol	Parameter	Conditions	f _{HCLK} (MHz)	Typ	Max ⁽¹⁾			Unit
					T _A = 25 °C	T _A = 85 °C	T _A = 105 °C	
I _{DD}	Supply current in Run mode	External clock, all peripherals enabled ⁽²⁾⁽³⁾	84	31.8	33	35	36	mA
			60	21.8	22	23	24	
			40	16.0	17	18	19	
			30	12.9	14	15	16	
			20	10.4	11	12	13	
		External clock, all peripherals disabled ⁽³⁾	84	21.2	22	23	24	
			60	15.0	16	17	18	
			40	10.9	12	13	14	
			30	8.8	10	11	12	
			20	7.1	8	9	10	

1. Guaranteed by characterization, unless otherwise specified.
2. Add an additional power consumption of 1.6 mA per ADC for the analog part. In applications, this consumption occurs only while the ADC is ON (ADON bit is set in the ADC_CR2 register).
3. When the ADC is ON (ADON bit set in the ADC_CR2), add an additional power consumption of 1.6mA per ADC for the analog part.

Table 26. Typical and maximum current consumption in Sleep mode

Symbol	Parameter	Conditions	f _{HCLK} (MHz)	Typ	Max ⁽¹⁾			Unit
					T _A = 25 °C	T _A = 85 °C	T _A = 105 °C	
I _{DD}	Supply current in Sleep mode	External clock, all peripherals enabled ⁽²⁾⁽³⁾	84	16.2	17	18	19	mA
			60	10.7	11	12	13	
			40	8.3	9	10	11	
			30	6.8	7	8	9	
			20	5.9	6	7	8	
		External clock, all peripherals disabled ⁽³⁾⁽⁴⁾	84	5.2	6	7	8	
			60	3.6	4	5	6	
			40	2.9	3	4	5	
			30	2.6	3	4	5	
			20	2.6	3	4	5	

1. Guaranteed by characterization, unless otherwise specified.
2. Add an additional power consumption of 1.6 mA per ADC for the analog part. In applications, this consumption occurs only while the ADC is ON (ADON bit is set in the ADC_CR2 register).
3. When the ADC is ON (ADON bit set in the ADC_CR2 register), add an additional power consumption of 1.6 mA for the analog part.
4. Same current consumption for f_{HCLK} at 30 MHz and 20 MHz due to VCO running slower at 30 MHz.

Table 30. Typical and maximum current consumption in Standby mode - $V_{DD}=3.3\text{ V}$

Symbol	Parameter	Conditions	Typ ⁽¹⁾	Max ⁽²⁾				Unit
			T _A = 25 °C	T _A = 25 °C	T _A = 85 °C	T _A = 105 °C		
I _{DD_STBY}	Supply current in Standby mode	Low-speed oscillator (LSE) and RTC ON	2.8	5.0	14.0	28.0	μA	
		RTC and LSE OFF	2.1	4.0 ⁽³⁾	13.0	27.0 ⁽³⁾		

1. When the PDR is OFF (internal reset is OFF), the typical current consumption is reduced by 1.2 μA .

2. Guaranteed by characterization, unless otherwise specified.

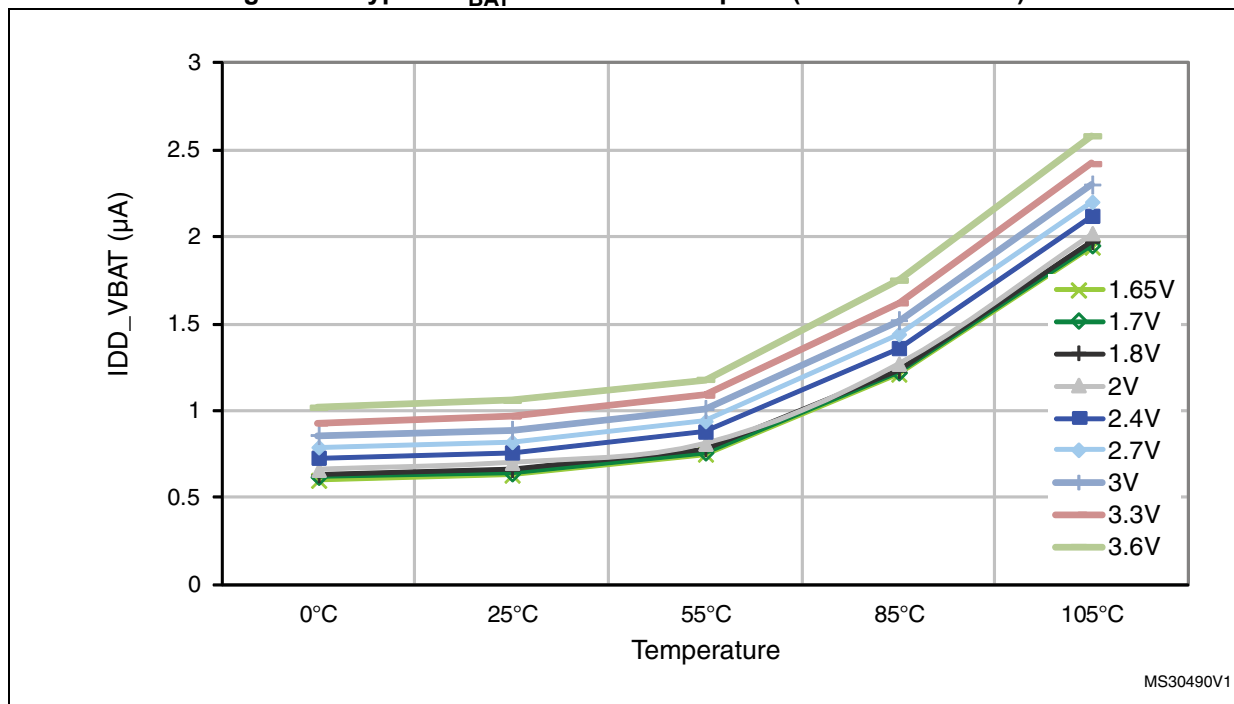
3. Guaranteed by test in production.

Table 31. Typical and maximum current consumptions in V_{BAT} mode

Symbol	Parameter	Conditions ⁽¹⁾	Typ			Max ⁽²⁾		Unit
			T _A = 25 °C			T _A = 85 °C	T _A = 105 °C	
			V _{BAT} = 1.7 V	V _{BAT} = 2.4 V	V _{BAT} = 3.3 V	V _{BAT} = 3.6 V		
I _{DD_VBAT}	Backup domain supply current	Low-speed oscillator (LSE) and RTC ON	0.66	0.76	0.97	3.0	5.0	μA
		RTC and LSE OFF	0.1	0.1	0.1	2.0	4.0	

1. Crystal used: Abracon ABS07-120-32.768 kHz-T with a C_L of 6 pF for typical values.

2. Guaranteed by characterization.

Figure 21. Typical V_{BAT} current consumption (LSE and RTC ON)

I/O system current consumption

The current consumption of the I/O system has two components: static and dynamic.

I/O static current consumption

All the I/Os used as inputs with pull-up generate current consumption when the pin is externally held low. The value of this current consumption can be simply computed by using the pull-up/pull-down resistors values given in [Table 54: I/O static characteristics](#).

For the output pins, any external pull-down or external load must also be considered to estimate the current consumption.

Additional I/O current consumption is due to I/Os configured as inputs if an intermediate voltage level is externally applied. This current consumption is caused by the input Schmitt trigger circuits used to discriminate the input value. Unless this specific configuration is required by the application, this supply current consumption can be avoided by configuring these I/Os in analog mode. This is notably the case of ADC input pins which should be configured as analog inputs.

Caution: Any floating input pin can also settle to an intermediate voltage level or switch inadvertently, as a result of external electromagnetic noise. To avoid current consumption related to floating pins, they must either be configured in analog mode, or forced internally to a definite digital value. This can be done either by using pull-up/down resistors or by configuring the pins in output mode.

I/O dynamic current consumption

In addition to the internal peripheral current consumption (see [Table 33: Peripheral current consumption](#)), the I/Os used by an application also contribute to the current consumption. When an I/O pin switches, it uses the current from the MCU supply voltage to supply the I/O pin circuitry and to charge/discharge the capacitive load (internal or external) connected to the pin:

$$I_{SW} = V_{DD} \times f_{SW} \times C$$

where

I_{SW} is the current sunk by a switching I/O to charge/discharge the capacitive load

V_{DD} is the MCU supply voltage

f_{SW} is the I/O switching frequency

C is the total capacitance seen by the I/O pin: $C = C_{INT} + C_{EXT}$

The test pin is configured in push-pull output mode and is toggled by software at a fixed frequency.

On-chip peripheral current consumption

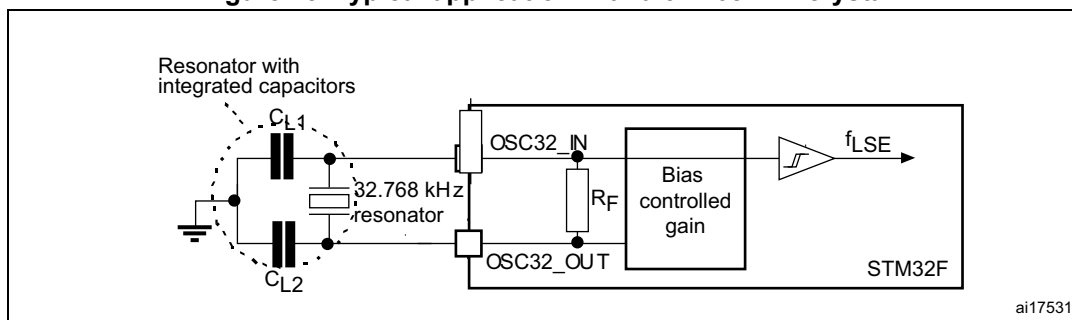
The MCU is placed under the following conditions:

- At startup, all I/O pins are in analog input configuration.
- All peripherals are disabled unless otherwise mentioned.
- The ART accelerator is ON.
- Voltage Scale 2 mode selected, internal digital voltage V12 = 1.26 V.
- HCLK is the system clock at 84 MHz. $f_{PCLK1} = f_{HCLK}/2$, and $f_{PCLK2} = f_{HCLK}$.
The given value is calculated by measuring the difference of current consumption
 - with all peripherals clocked off
 - with only one peripheral clocked on
- Ambient operating temperature is 25 °C and $V_{DD}=3.3$ V.

Table 33. Peripheral current consumption

Peripheral		I _{DD} (typ)	Unit
AHB1 (up to 84MHz)	GPIOA	1.55	μA/MHz
	GPIOB	1.55	
	GPIOC	1.55	
	GPIOD	1.55	
	GPIOE	1.55	
	GPIOH	1.55	
	CRC	0.36	
	DMA1	20.24	
	DMA2	21.07	
APB1 (up to 42MHz)	TIM2	11.19	μA/MHz
	TIM3	8.57	
	TIM4	8.33	
	TIM5	11.19	
	PWR	0.71	
	USART2	3.33	
	I2C1/2/3	3.10	
	SPI2 ⁽¹⁾	2.62	
	SPI3 ⁽¹⁾	2.86	
	I2S2	1.90	
	I2S3	1.67	
	WWDG	0.71	
AHB2 (up to 84MHz)	OTG_FS	23.93	μA/MHz

Figure 25. Typical application with a 32.768 kHz crystal



6.3.9 Internal clock source characteristics

The parameters given in [Table 39](#) and [Table 40](#) are derived from tests performed under ambient temperature and V_{DD} supply voltage conditions summarized in [Table 14](#).

High-speed internal (HSI) RC oscillator

Table 39. HSI oscillator characteristics ⁽¹⁾

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{HSI}	Frequency	-	-	16	-	MHz
ACC_{HSI}	HSI user trimming step ⁽²⁾	-	-	-	1	%
	Accuracy of the HSI oscillator	$T_A = -40$ to $105\text{ }^{\circ}\text{C}^{(3)}$	-8	-	4.5	%
		$T_A = -10$ to $85\text{ }^{\circ}\text{C}^{(3)}$	-4	-	4	%
		$T_A = 25\text{ }^{\circ}\text{C}^{(4)}$	-1	-	1	%
$t_{su(HSI)}^{(2)}$	HSI oscillator startup time	-	-	2.2	4	μs
$I_{DD(HSI)}^{(2)}$	HSI oscillator power consumption	-	-	60	80	μA

1. $V_{DD} = 3.3\text{ V}$, $T_A = -40$ to $105\text{ }^{\circ}\text{C}$ unless otherwise specified.

2. Guaranteed by design.

3. Guaranteed by characterization.

4. Factory calibrated, parts not soldered.

Table 48. EMS characteristics for LQFP100 package

Symbol	Parameter	Conditions	Level/Class
V_{FESD}	Voltage limits to be applied on any I/O pin to induce a functional disturbance	$V_{DD} = 3.3\text{ V}$, LQFP100, WLCSP49, $T_A = +25\text{ }^{\circ}\text{C}$, $f_{HCLK} = 84\text{ MHz}$, conforms to IEC 61000-4-2	2B
V_{EFTB}	Fast transient voltage burst limits to be applied through 100 pF on V_{DD} and V_{SS} pins to induce a functional disturbance	$V_{DD} = 3.3\text{ V}$, LQFP100, WLCSP49, $T_A = +25\text{ }^{\circ}\text{C}$, $f_{HCLK} = 84\text{ MHz}$, conforms to IEC 61000-4-4	4A

When the application is exposed to a noisy environment, it is recommended to avoid pin exposition to disturbances. The pins showing a middle range robustness are: PA0, PA1, PA2, on LQFP100 packages and PDR_ON on WLCSP49.

As a consequence, it is recommended to add a serial resistor (1 k Ω maximum) located as close as possible to the MCU to the pins exposed to noise (connected to tracks longer than 50 mm on PCB).

Designing hardened software to avoid noise problems

EMC characterization and optimization are performed at component level with a typical application environment and simplified MCU software. It should be noted that good EMC performance is highly dependent on the user application and the software in particular.

Therefore it is recommended that the user applies EMC software optimization and prequalification tests in relation with the EMC level requested for his application.

Software recommendations

The software flowchart must include the management of runaway conditions such as:

- Corrupted program counter
- Unexpected reset
- Critical Data corruption (control registers...)

Prequalification trials

Most of the common failures (unexpected reset and program counter corruption) can be reproduced by manually forcing a low state on the NRST pin or the Oscillator pins for 1 second.

To complete these trials, ESD stress can be applied directly on the device, over the range of specification values. When unexpected behavior is detected, the software can be hardened to prevent unrecoverable errors occurring (see application note AN1015).

Table 54. I/O static characteristics (continued)

Symbol	Parameter		Conditions	Min	Typ	Max	Unit
V _{HYS}	FT and NRST I/O input hysteresis		1.7 V≤V _{DD} ≤3.6 V	-	10% V _{DD} ⁽³⁾	-	V
	BOOT0 I/O input hysteresis		1.75 V≤V _{DD} ≤3.6 V, -40 °C≤T _A ≤105 °C	-	100	-	mV
			1.7 V≤V _{DD} ≤3.6 V, 0 °C≤T _A ≤105 °C				
I _{Ikg}	I/O input leakage current ⁽⁴⁾		V _{SS} ≤V _{IN} ≤V _{DD}	-	-	±1	μA
	I/O FT input leakage current ⁽⁵⁾		V _{IN} = 5 V	-	-	3	
R _{PU}	Weak pull-up equivalent resistor ⁽⁶⁾	All pins except for PA10 (OTG_FS_ID)	V _{IN} = V _{SS}	30	40	50	kΩ
		PA10 (OTG_FS_ID)		7	10	14	
R _{PD}	Weak pull-down equivalent resistor ⁽⁷⁾	All pins except for PA10 (OTG_FS_ID)	V _{IN} = V _{DD}	30	40	50	
		PA10 (OTG_FS_ID)		7	10	14	
C _{IO} ⁽⁸⁾	I/O pin capacitance		-	-	5	-	pF

1. Guaranteed by design.

2. Guaranteed by test in production.

3. With a minimum of 200 mV.

4. Leakage could be higher than the maximum value, if negative current is injected on adjacent pins, Refer to [Table 53: I/O current injection susceptibility](#)

5. To sustain a voltage higher than $V_{DD} + 0.3\text{ V}$, the internal pull-up/pull-down resistors must be disabled. Leakage could be higher than the maximum value, if negative current is injected on adjacent pins. Refer to [Table 53: I/O current injection susceptibility](#)

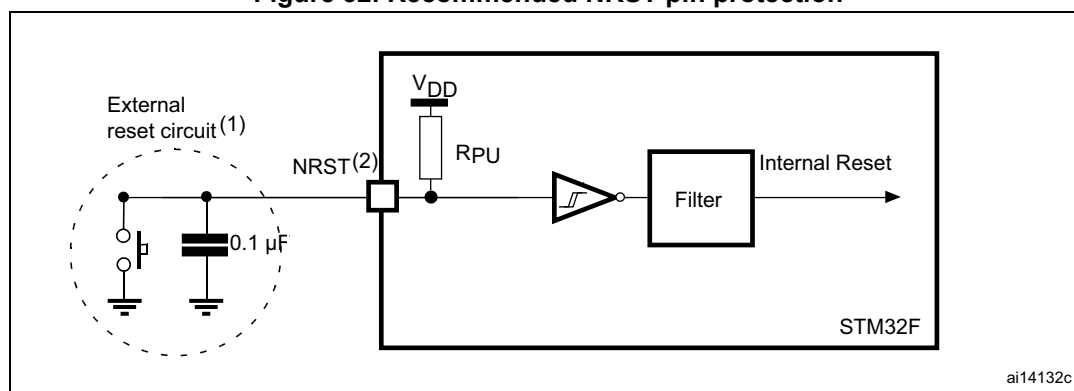
6. Pull-up resistors are designed with a true resistance in series with a switchable PMOS. This PMOS contribution to the series resistance is minimum (~10% order).

7. Pull-down resistors are designed with a true resistance in series with a switchable NMOS. This NMOS contribution to the series resistance is minimum (~10% order).

8. Hysteresis voltage between Schmitt trigger switching levels. Guaranteed by characterization.

All I/Os are CMOS and TTL compliant (no software configuration required). Their characteristics cover more than the strict CMOS-technology or TTL parameters. The coverage of these requirements for FT I/Os is shown in [Figure 30](#).

Figure 32. Recommended NRST pin protection



1. The reset network protects the device against parasitic resets.
2. The external capacitor must be placed as close as possible to the device.
3. The user must ensure that the level on the NRST pin can go below the $V_{IL(NRST)}$ max level specified in [Table 57](#). Otherwise the reset is not taken into account by the device.

6.3.18 TIM timer characteristics

The parameters given in [Table 58](#) are guaranteed by design.

Refer to [Section 6.3.16: I/O port characteristics](#) for details on the input/output alternate function characteristics (output compare, input capture, external clock, PWM output).

Table 58. TIMx characteristics⁽¹⁾⁽²⁾

Symbol	Parameter	Conditions ⁽³⁾	Min	Max	Unit
$t_{res(TIM)}$	Timer resolution time	AHB/APBx prescaler=1 or 2 or 4, $f_{TIMxCLK} = 84\text{ MHz}$	1	-	$t_{TIMxCLK}$
			11.9	-	ns
		AHB/APBx prescaler>4, $f_{TIMxCLK} = 84\text{ MHz}$	1	-	$t_{TIMxCLK}$
			11.9	-	ns
f_{EXT}	Timer external clock frequency on CH1 to CH4	$f_{TIMxCLK} = 84\text{ MHz}$	0	$f_{TIMxCLK}/2$	MHz
			0	42	MHz
Res_{TIM}	Timer resolution		-	16/32	bit
$t_{COUNTER}$	16-bit counter clock period when internal clock is selected	$f_{TIMxCLK} = 84\text{ MHz}$	0.0119	780	μs
t_{MAX_COUNT}	Maximum possible count with 32-bit counter		-	65536×65536	$t_{TIMxCLK}$
		$f_{TIMxCLK} = 84\text{ MHz}$	-	51.1	S

1. TIMx is used as a general term to refer to the TIM1 to TIM11 timers.
2. Guaranteed by design.
3. The maximum timer frequency on APB1 is 42 MHz and on APB2 is up to 84 MHz, by setting the TIMPRE bit in the RCC_DCKCFGR register, if APBx prescaler is 1 or 2 or 4, then $TIMxCLK = HCLK$, otherwise $TIMxCLK \geq 4 \times PCLKx$.

SPI interface characteristics

Unless otherwise specified, the parameters given in [Table 61](#) for the SPI interface are derived from tests performed under the ambient temperature, f_{PCLKx} frequency and V_{DD} supply voltage conditions summarized in [Table 14](#), with the following configuration:

- Output speed is set to $OSPEEDRy[1:0] = 10$
- Capacitive load $C = 30$ pF
- Measurement points are done at CMOS levels: $0.5V_{DD}$

Refer to [Section 6.3.16: I/O port characteristics](#) for more details on the input/output alternate function characteristics (NSS, SCK, MOSI, MISO for SPI).

Table 61. SPI dynamic characteristics⁽¹⁾

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{SCK} $1/t_{c(SCK)}$	SPI clock frequency	Master mode, SPI1/4, $2.7\text{ V} < V_{DD} < 3.6\text{ V}$	-	-	42	MHz
		Slave mode, SPI1/4, $2.7\text{ V} < V_{DD} < 3.6\text{ V}$			42	
		Slave transmitter/full-duplex mode, SPI1/4, $2.7\text{ V} < V_{DD} < 3.6\text{ V}$			38 ⁽²⁾	
		Master mode, SPI1/2/3/4, $1.7\text{ V} < V_{DD} < 3.6\text{ V}$			21	
		Slave mode, SPI1/2/3/4, $1.7\text{ V} < V_{DD} < 3.6\text{ V}$			21	
Duty(SCK)	Duty cycle of SPI clock frequency	Slave mode	30	50	70	%
$t_{w(SCKH)}$ $t_{w(SCKL)}$	SCK high and low time	Master mode, SPI presc = 2	$T_{PCLK}-1.5$	T_{PCLK}	$T_{PCLK}+1.5$	ns
$t_{su(NSS)}$	NSS setup time	Slave mode, SPI presc = 2	$4T_{PCLK}$	-	-	ns
$t_h(NSS)$	NSS hold time	Slave mode, SPI presc = 2	$2T_{PCLK}$	-	-	ns
$t_{su(MI)}$	Data input setup time	Master mode	0	-	-	ns
$t_{su(SI)}$		Slave mode	2.5	-	-	ns
$t_h(MI)$	Data input hold time	Master mode	6	-	-	ns
$t_h(SI)$		Slave mode	2.5	-	-	ns
$t_a(SO)$	Data output access time	Slave mode	9	-	20	ns
$t_{dis(SO)}$	Data output disable time	Slave mode	8	-	13	ns
$t_v(SO)$	Data output valid time	Slave mode (after enable edge), $2.7\text{ V} < V_{DD} < 3.6\text{ V}$	-	9.5	13	ns
		Slave mode (after enable edge), $1.7\text{ V} < V_{DD} < 3.6\text{ V}$	-	9.5	17	ns
$t_h(SO)$	Data output hold time	Slave mode (after enable edge), $2.7\text{ V} < V_{DD} < 3.6\text{ V}$	5.5	-	-	ns
		Slave mode (after enable edge), $1.7\text{ V} < V_{DD} < 3.6\text{ V}$	3.5	-	-	ns

Table 66. ADC characteristics (continued)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$t_{lat}^{(2)}$	Injection trigger conversion latency	$f_{ADC} = 30\text{ MHz}$	-	-	0.100	μs
			-	-	3 ⁽⁵⁾	$1/f_{ADC}$
$t_{latr}^{(2)}$	Regular trigger conversion latency	$f_{ADC} = 30\text{ MHz}$	-	-	0.067	μs
			-	-	2 ⁽⁵⁾	$1/f_{ADC}$
$t_S^{(2)}$	Sampling time	$f_{ADC} = 30\text{ MHz}$	0.100	-	16	μs
			3	-	480	$1/f_{ADC}$
$t_{STAB}^{(2)}$	Power-up time		-	2	3	μs
$t_{CONV}^{(2)}$	Total conversion time (including sampling time)	$f_{ADC} = 30\text{ MHz}$ 12-bit resolution	0.50	-	16.40	μs
		$f_{ADC} = 30\text{ MHz}$ 10-bit resolution	0.43	-	16.34	μs
		$f_{ADC} = 30\text{ MHz}$ 8-bit resolution	0.37	-	16.27	μs
		$f_{ADC} = 30\text{ MHz}$ 6-bit resolution	0.30	-	16.20	μs
		9 to 492 (t_S for sampling +n-bit resolution for successive approximation)				$1/f_{ADC}$
$f_S^{(2)}$	Sampling rate ($f_{ADC} = 30\text{ MHz}$, and $t_S = 3\text{ ADC cycles}$)	12-bit resolution Single ADC	-	-	2	Msp/s
		12-bit resolution Interleave Dual ADC mode	-	-	3.75	Msp/s
		12-bit resolution Interleave Triple ADC mode	-	-	6	Msp/s
$I_{VREF+}^{(2)}$	ADC V_{REF} DC current consumption in conversion mode		-	300	500	μA
$I_{VDDA}^{(2)}$	ADC V_{DDA} DC current consumption in conversion mode		-	1.6	1.8	mA

1. V_{DDA} minimum value of 1.7 V is possible with the use of an external power supply supervisor (refer to [Section 3.14.2: Internal reset OFF](#)).
2. Guaranteed by characterization.
3. V_{REF+} is internally connected to V_{DDA} and V_{REF-} is internally connected to V_{SSA} .
4. R_{ADC} maximum value is given for $V_{DD}=1.7\text{ V}$, and minimum value for $V_{DD}=3.3\text{ V}$.
5. For external triggers, a delay of $1/f_{CLK2}$ must be added to the latency specified in [Table 66](#).

Table 70. ADC dynamic accuracy at $f_{\text{ADC}} = 18 \text{ MHz}$ - limited test conditions⁽¹⁾

Symbol	Parameter	Test conditions	Min	Typ	Max	Unit
ENOB	Effective number of bits	$f_{\text{ADC}} = 18 \text{ MHz}$ $V_{\text{DDA}} = V_{\text{REF+}} = 1.7 \text{ V}$ Input Frequency = 20 KHz Temperature = 25 °C	10.3	10.4	-	bits
SINAD	Signal-to-noise and distortion ratio		64	64.2	-	dB
SNR	Signal-to-noise ratio		64	65	-	
THD	Total harmonic distortion		-67	-72	-	

1. Guaranteed by characterization.

Table 71. ADC dynamic accuracy at $f_{\text{ADC}} = 36 \text{ MHz}$ - limited test conditions⁽¹⁾

Symbol	Parameter	Test conditions	Min	Typ	Max	Unit
ENOB	Effective number of bits	$f_{\text{ADC}} = 36 \text{ MHz}$ $V_{\text{DDA}} = V_{\text{REF+}} = 3.3 \text{ V}$ Input Frequency = 20 KHz Temperature = 25 °C	10.6	10.8	-	bits
SINAD	Signal-to noise and distortion ratio		66	67	-	dB
SNR	Signal-to noise ratio		64	68	-	
THD	Total harmonic distortion		-70	-72	-	

1. Guaranteed by characterization.

Note: ADC accuracy vs. negative injection current: injecting a negative current on any analog input pins should be avoided as this significantly reduces the accuracy of the conversion being performed on another analog input. It is recommended to add a Schottky diode (pin to ground) to analog pins which may potentially inject negative currents.

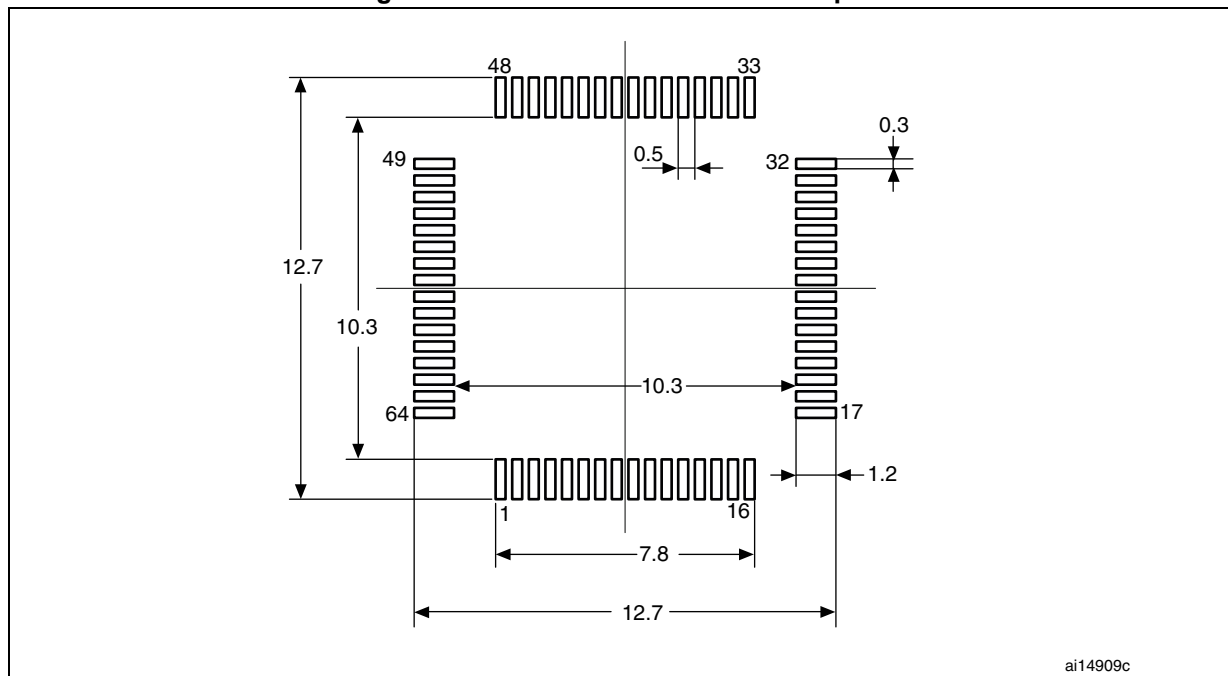
Any positive injection current within the limits specified for $I_{\text{INJ(PIN)}}$ and $\Sigma I_{\text{INJ(PIN)}}$ in [Section 6.3.16](#) does not affect the ADC accuracy.

Table 82. LQFP64 - 64-pin, 10 x 10 mm, 64-pin low-profile quad flat package mechanical data

Symbol	millimeters			inches ⁽¹⁾		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	-	-	1.600	-	-	0.0630
A1	0.050	-	0.150	0.0020	-	0.0059
A2	1.350	1.400	1.450	0.0531	0.0551	0.0571
b	0.170	0.220	0.270	0.0067	0.0087	0.0106
c	0.090	-	0.200	0.0035	-	0.0079
D	-	12.000	-	-	0.4724	-
D1	-	10.000	-	-	0.3937	-
E	-	12.000	-	-	0.4724	-
E1	-	10.000	-	-	0.3937	-
E3	-	7.5000	-	-	0.2953	-
e	-	0.500	-	-	0.0197	-
K	0°	3.5°	7°	0°	3.5°	7°
L	0.450	0.600	0.750	0.0177	0.0236	0.0295
L1	-	1.000	-	-	0.0394	-
ccc	-	-	0.080	-	-	0.0031

1. Values in inches are converted from mm and rounded to 4 decimal digits.

Figure 53. LQFP64 recommended footprint



1. Dimensions are in millimeters.